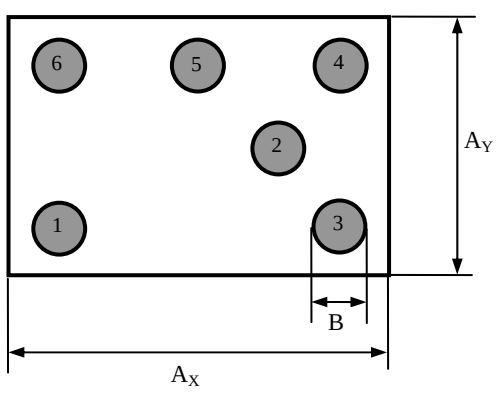
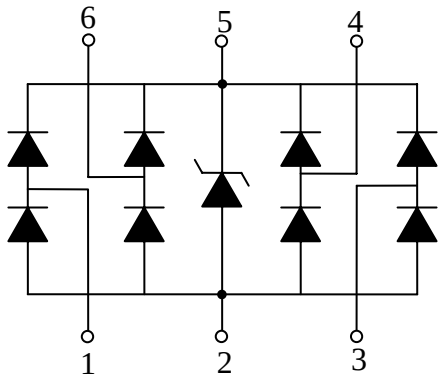
VSP-MIKRON

Rev.1. March 2010.

KS-05V4

Chip for dual USB 2.0 Integrated ESD protection to IEC 61000-4-2 level 4.





Mechanical date: A_x= 800um, A_y=580um, B=90um
Chip thickness: 230+/-20 um
Scribe Line width - 60um.
Top Metal: Al - for wire bonding.
Back side - Anode: Ti-Ni-Ag for soldering.

Schematic and pinning diagram.

Limiting values

Parameter	Symbol	Conditions	Value	Unit
DC input voltage range	$V_{I/O}$	-	+5.5 max	V
Electrostatic Discharge	V_{ESD}	IEC 61000-4-2, level 4.	±8.0 (Contact)	kV
Max. junction temperature	T_j	-	+125	ºC

Characteristics (Tj=25ºC)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{lkg}	Diode reverses leakage current. Pins 1, 3, 4, 6 to ground	V=+3,0 V	-	-	100	nA
V_{BR}	Zener diode breakdown voltage. Pin 5 to 2.	I_Z=1mA	6,1	7,0	8,5	V
C_z	Zener diode capacitance to ground. Pin 5 to 2.	F=1MHz, V_{dc}=0 V. Pin 5 = +3,0 V	-	40	-	pF
V_F	Forward voltage	I_F=1mA	-	0,7	-	V
$C_{I/O}$	Pin capacitance to ground. Pins 1, 3, 4, 6 to 2.	V_{dc}=0 V; f =1MHz. Pin 5 = +3,0 V	-	1,0	-	pF

*- For Device testing